

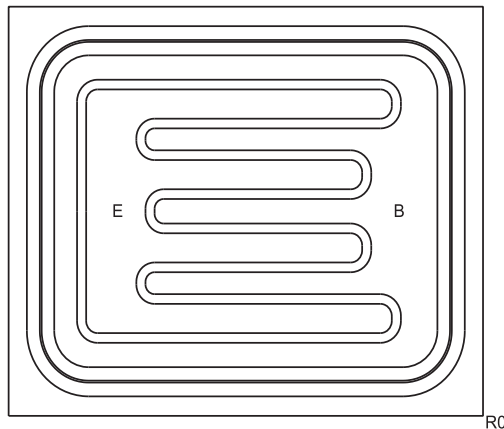
PROCESS CP611
Power Transistor
PNP - Amp/Switch Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	80 x 99 MILS
Die Thickness	12.5 $\pm$ 1 MILS
Base Bonding Pad Area	12 x 32 MILS
Emitter Bonding Pad Area	13 x 46 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Ag - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

1,300

PRINCIPAL DEVICE TYPES

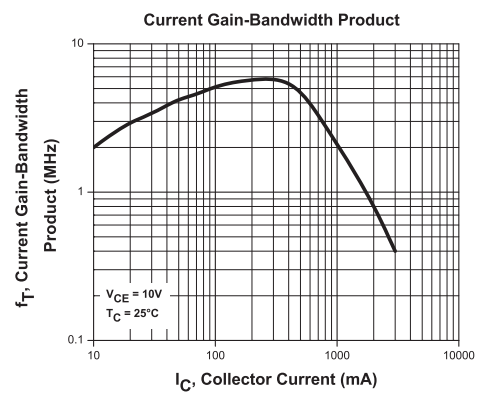
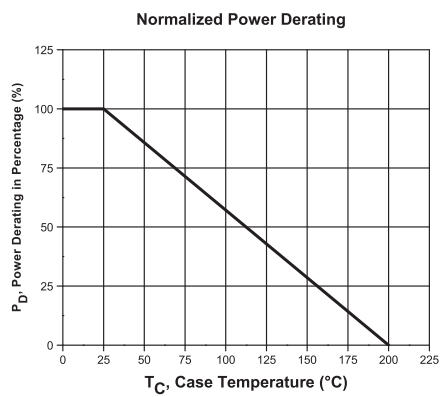
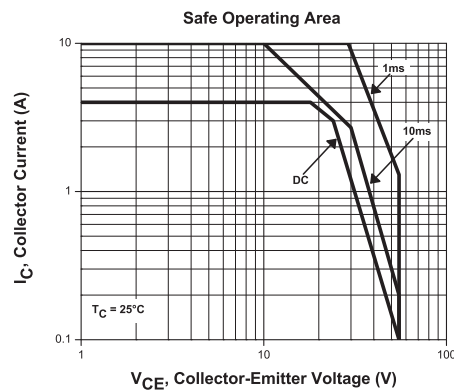
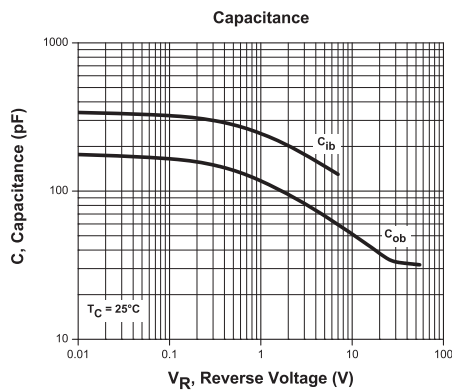
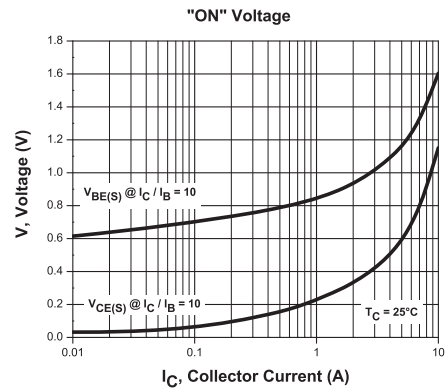
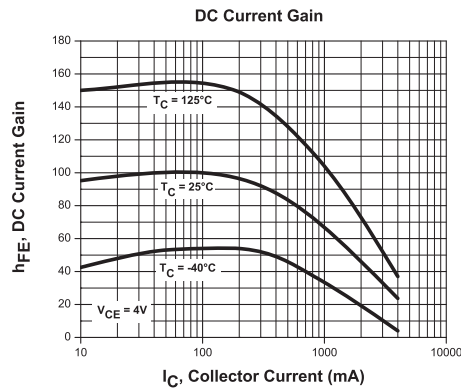
CJD42C

TIP42C

R5 (22-March 2010)

PROCESS CP611

Typical Electrical Characteristics



R5 (22-March 2010)